

CD4508B Types

CMOS Dual 4-Bit Latch

High-Voltage Types (20-Volt Rating)

CD4508B dual 4-bit latch contains two identical 4-bit latches with separate STROBE, RESET, and OUTPUT DISABLE controls. With the STROBE line in the high state, the data on the "D" inputs appear at the corresponding "Q" outputs provided the DISABLE line is in the low state. Changing the STROBE line to the low state locks the data into the latch. A high on the reset line forces the outputs to a low level regardless of the state of the STROBE input. The outputs are forced to the high-impedance state for bus line applications by a high level on the DISABLE input.

The CD4508B types are supplied in 24-lead hermetic dual-in-line ceramic packages (F3A suffix), 24-lead dual-in-line plastic packages (E suffix), 24-lead small-outline packages (M, M96, and NSR suffixes), and 24-lead thin shrink small-outline packages (PW and PWR suffixes).

The CD4508B is similar to industry type MC14508.

Features:

- Two independent 4-bit latches
- Individual master reset for each 4-bit latch
- 3-state outputs with high-impedance state for bus line applications
- Medium-speed operation: tpHL = tpLH = 70 ns (typ.) at VDD = 10 V and CL = 50 pF
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) =

1 V at VDD = 5 V

2 V at V_{DD} = 10 V

 $2.5 \text{ V at V}_{DD} = 15 \text{ V}$

 Meets all requirements of JEDEC Tentative Standard No. 13B,"Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

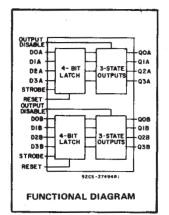
- **■** Buffer storage
- Holding registers
- Data storage and multiplexing

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (VDD)
Voltages referenced to V _{SS} Terminal)0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to VDD +0.5V
DC INPUT CURRENT, ANY ONE INPUT ±10mA
POWER DISSIPATION PER PACKAGE (PD):
For T _A = -55°C to +100°C
For T _A = +100°C to +125°C Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (T _A)55°C to +125°C
STORAGE TEMPERATURE RANGE (T _{stg})65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}$ C, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	V _{DD}	LIM	ITS	
CHARACTERISTIC	(V)	Min.	Max.	UNITS
Supply-Voltage Range (For TA = Full Package- Temperature Range)		3	18	٧
	5	200	_	
Reset Pulse Width, tW(R)	10	140	-	
, ,	15	100	-	
	5	140	_	
Strobe Pulse Width, tW(st)	10	80	_	
	15	70		200
	5	50	_	ns
Setup Time, t _{SU}	10	30	_	
	15	20	_	
	5	0	-	
Hold Time, tH	10	0	_	
	15	0	_	



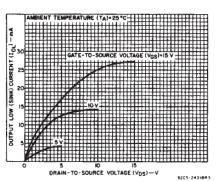


Fig.2 — Typical output low (sink) current characteristics.

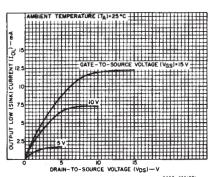


Fig.3 – Minimum output low (sink) current characteristics.

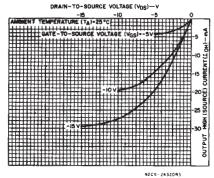


Fig.4 — Typical output high (source) current

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONE	OITIO	IS	LIMIT	LIMITS AT INDICATED TEMPERATURES (°C)						
ISTIC	Vo	VIN	VDD						+25		UNIT
	(V)	(V)	(V)	-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device	-	0,5	5	5	5	150	150	-	0.04	.5	
Current,	_	0,10	10	10	10	300	300		0.04	10	μΑ
IDD Max.		0,15	15	. 20	20	600	600		0.04	20	μ~
		0,20	20	100	100	3000	3000	- 1,	0.08	100	}
Output Low	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1		
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6		
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	34	6.8	_	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	- "	mA
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	, s, 	
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	.'-	
TOPI IIII.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	100
Output Voltage:	_	0,5	5		0	.05			0	0.05	
Low-Level, VOL Max.	_	0,10	10		0	.05		-	0	0.05	
AOF Max.	_	0,15	15		0	.05		_	0	0.05	. v
Output Voltage:	_	0,5	5	4.95				4.95	5	-	•
High-Level,	_	0,10	10		9	95		9.95	10	-	
VOH Min.	_	0,15	15		14	.95		14.95	15	7 (**** ·	
Input Low	0.5, 4.5	_	5		1	.5		_	_	1.5	
Voltage,	1, 9	-	10			3			- 122	3	4 - 4
VIL Max.	1.5,13.5	_	15		4					4	v
Input High	0.5, 4.5	_	5		3	1.5		3.5	-		V
Voltage,	. 1, 9	_	10			7		7	_	_	
VIH Min.	1.5,13.5	- - - 1	15		1	1		11	_	_	
Input Current	_	0,18	18	±0.1	±0.1	±1	±1	ı	±10 ⁻⁵	±0.1	μΑ
3-State Output Leakage Current IOUT Max.	0,18	0,18	18	±0.4	±0.4	±12	±12		±10-4	±0.4	μΑ

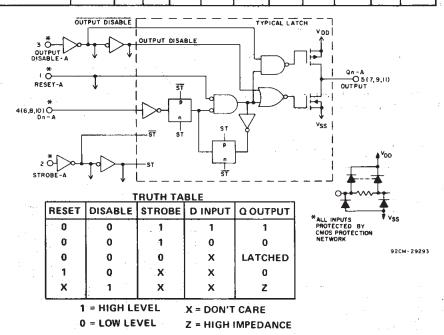


Fig. 7 — Logic diagram (A-Section), 1 of 4 identical latches with common output disable, reset, and strobe.

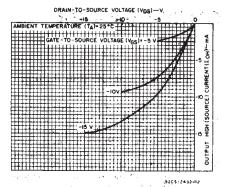


Fig. 4 — Minimum output high (source) current characteristics.

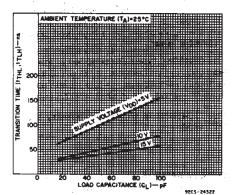


Fig. 5 — Typical transition time as a function of load capacitance.

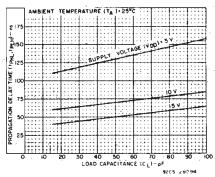


Fig. 6 — Typical propagation delay time as a function of load capacitance (strobe to data out).

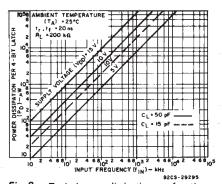
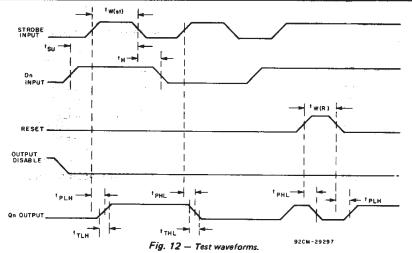


Fig. 8 — Typical power dissipation as a function of frequency.

CD4508B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_f, t_f = 20 ns, C_L = 50 pF, R_L = 200 k Ω , unless otherwise specified.

OUA DA OTE DIATIO	TEST		LIA	MITS	
CHARACTERISTIC	CONDITIONS	VDD	Тур.	Max.	UNITS
		5	100	200	-
Transition Time, tthe, ttel	İ	10	50	100	ļ
		15	40	80	
		5	100	200	1
Minimum Reset Pulse Width, tW(R)	1	10	70	140	ľ
44(14)		15	50	100	
		5	70	140	1
Minimum Strobe Pulse Width, tW(st)		10	40	80	
44/2()		15	35	70	
		5	25	50	
Minimum Setup Time, t _{SU}		10	15	30	
30		15	10	20	
		5	0	0	
Minimum Hold Time, t _H		10	ō	ő	
n de la companya de La companya de la co		15	0	ō	
Propagation Delay Times: tpHL,tpLH		5	130	260	
Strobe to Data Out		10	70	140	
otrobe to Data Out		15	50	100	ns
	1	5	105	210	113
Data In to Data Out	•	10	60	120	7
		15	45	90	
		5	90	180	
Reset to Data Out		10	50	100	
<u> </u>		15	40	80	
		5	90	180	
3-State Propagation Delay Times:		10	50	100	
Output High to High Impedance, tpHZ		15	35	70	
		5	90	180	
High Impedance to Output High, tpZH		10	50 50	100	
		15	35	70	
		5	90	180	
Output Low to High Impedance, tpLZ	[10	50 50	100	
Corpor com to riigh improduce, tPLZ		15	35	70	
		5	90	180	
High Impedance to Output Low, tpZL		10	50	100	. '
		15	35	70	
Input Capacitance, CIN	Any Input	-	5	7.5	pF



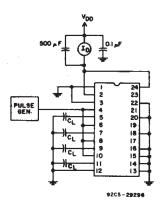


Fig.9 - Power dissipation test circuit.

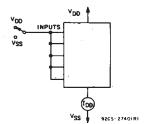


Fig. 10 — Quiescent device current test circuit.

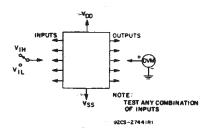


Fig.11 - Input voltage test circuit.

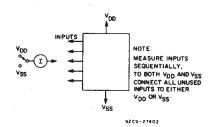


Fig. 13 - Input current test circuit.

CD4508B Types

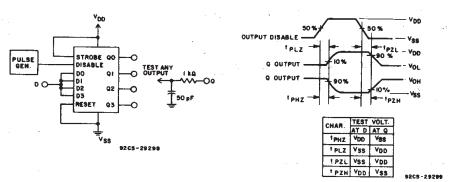


Fig. 14 - Output disable test circuit and waveforms.

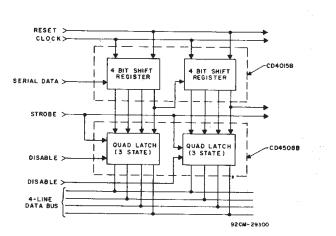
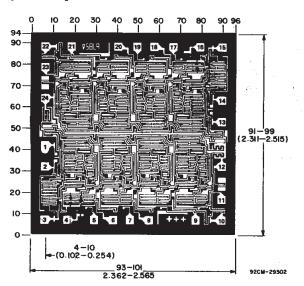
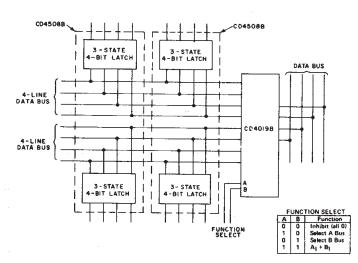


Fig. 15 - Bus register.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

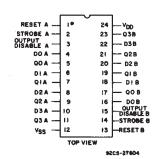
Chip dimensions and pad layout for CD4508B.



92CM-29301

Fig. 16 — Dual multiplexed bus register with

function select.



TERMINAL ASSIGNMENT

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CD4508BD3	ACTIVE	CDIP SB	JD	24	1	TBD	POST-PLATE	N / A for Pkg Type	-55 to 125	CD4508BD/3	Samples
CD4508BF3A	ACTIVE	CDIP	J	24	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	CD4508BF3A	Samples
CD4508BM	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508BM	Samples
CD4508BM96	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508BM	Samples
CD4508BME4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508BM	Samples
CD4508BNSR	ACTIVE	so	NS	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4508B	Samples
CD4508BPW	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM508B	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD4508B, CD4508B-MIL:

Catalog: CD4508B

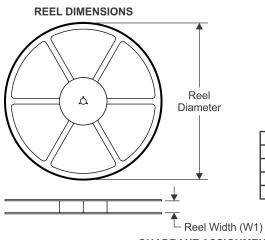
Military: CD4508B-MIL

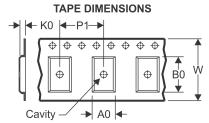
NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

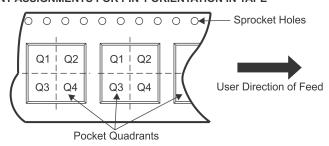
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

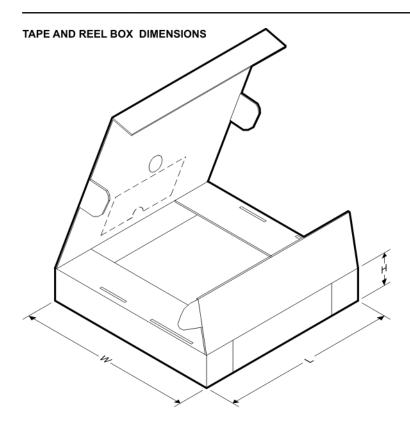
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD4508BM96	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CD4508BNSR	SO	NS	24	2000	330.0	24.4	8.3	15.4	2.6	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION



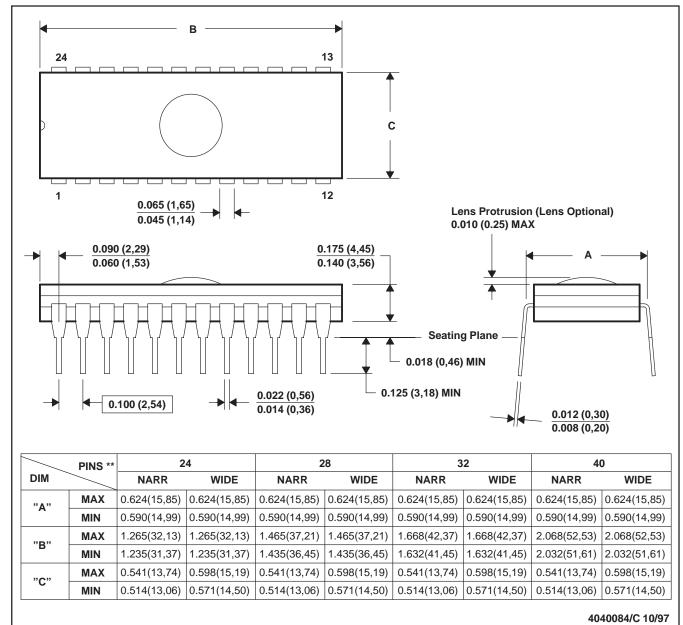
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD4508BM96	SOIC	DW	24	2000	367.0	367.0	45.0
CD4508BNSR	SO	NS	24	2000	367.0	367.0	45.0

J (R-GDIP-T**)

CERAMIC DUAL-IN-LINE PACKAGE

24 PINS SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

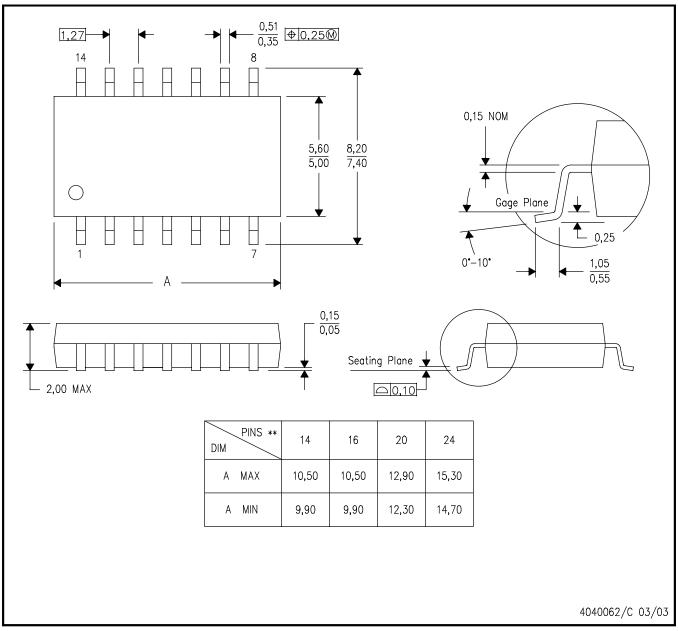
- B. This drawing is subject to change without notice.
- C. Window (lens) added to this group of packages (24-, 28-, 32-, 40-pin).
- D. This package can be hermetically sealed with a ceramic lid using glass frit.
- E. Index point is provided on cap for terminal identification.

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE

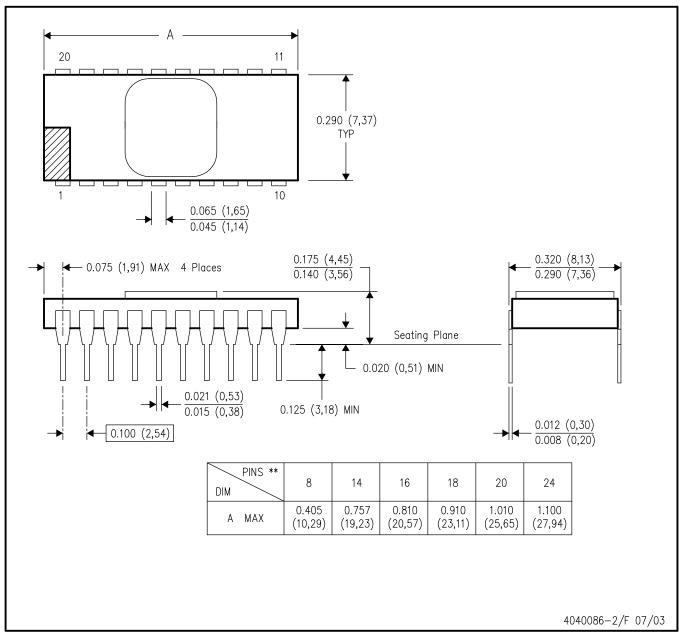


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

JD (R-CDIP-T**)

CERAMIC SIDE-BRAZE DUAL-IN-LINE PACKAGE

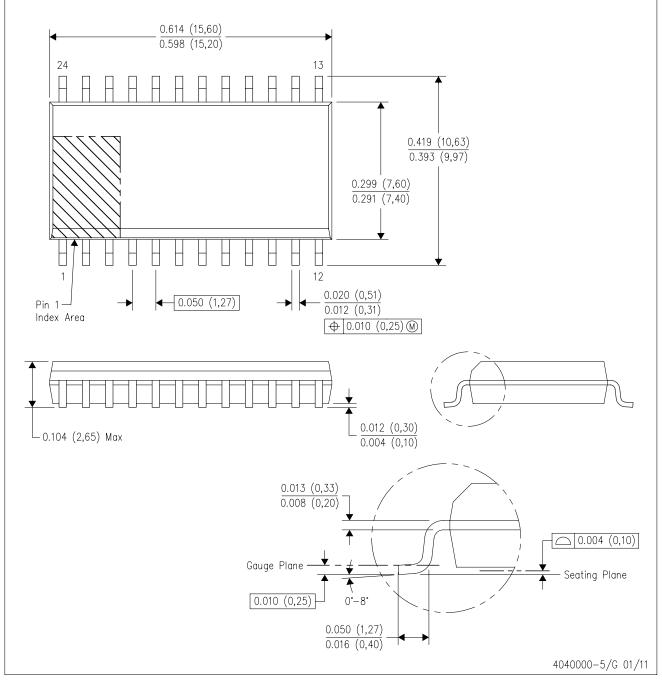
20 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within MIL STD 1835 CDIP2 T8, T14, T16, T18, T20 and T24 respectively.

DW (R-PDSO-G24)

PLASTIC SMALL OUTLINE

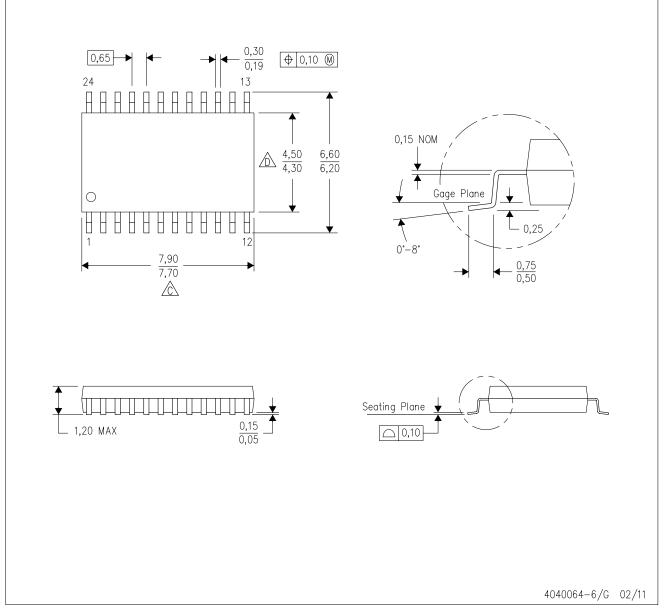


NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.

PW (R-PDSO-G24)

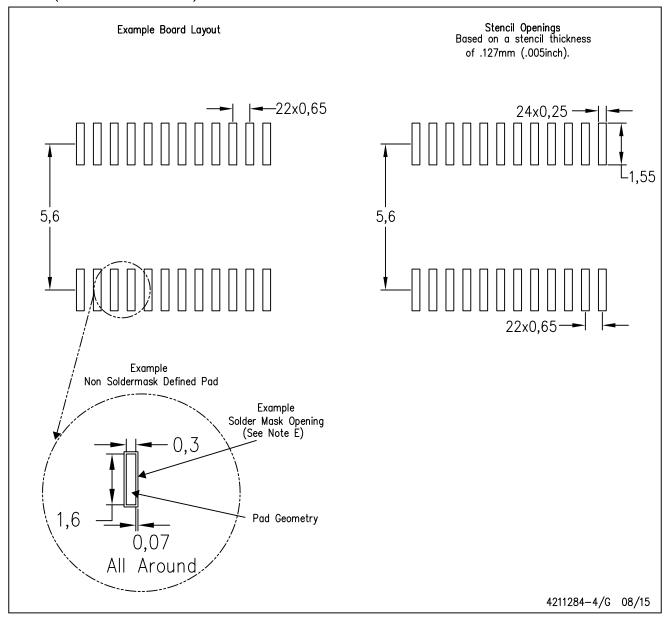
PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153

PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.